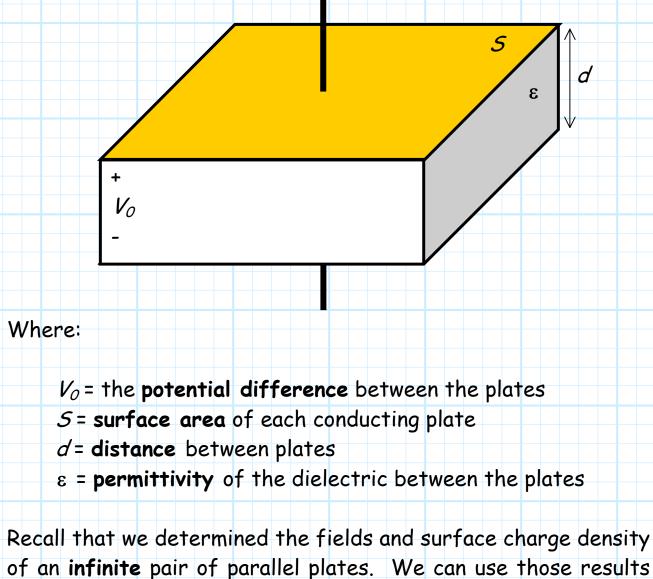
<u>The Parallel</u> <u>Plate Capacitor</u>

Consider the geometry of a **parallel plate capacitor**:

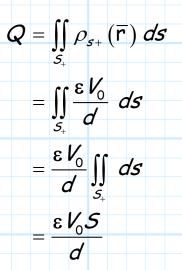


to approximate the fields and charge densities of this **finite** structure, where the **area** of each plate is *S*.

For example, we determined that the **surface charge density** on the upper plate is:

$$\rho_{s+}\left(\overline{\mathbf{r}}\right) = \frac{\varepsilon V_0}{d}$$

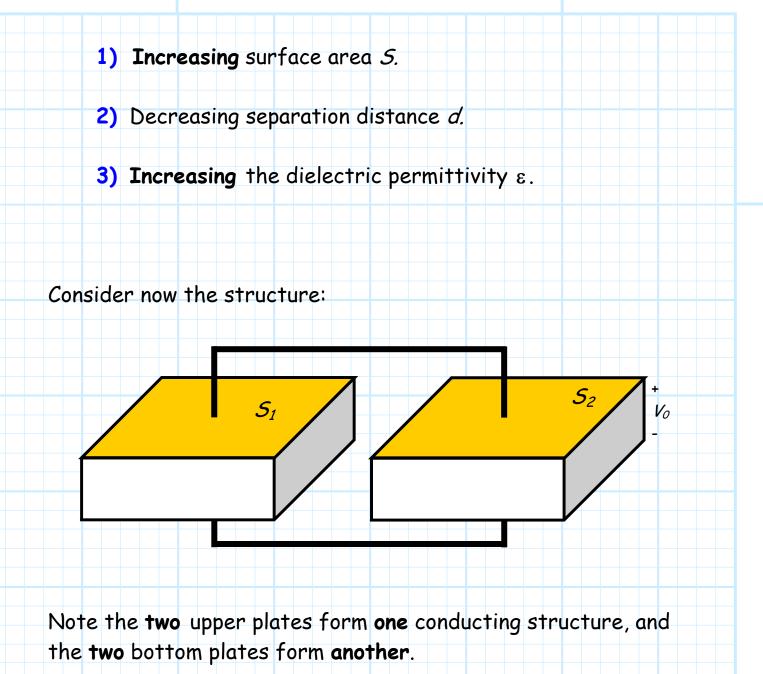
The total charge on the upper plate is therefore:



The **capacitance** of this structure is therefore:

$$C = \frac{Q}{V} = \left(\frac{\varepsilon V_0 S}{d}\right) \left(\frac{1}{V_0}\right) = \frac{\varepsilon S}{d} \quad [Farads]$$

Note therefore, that we can **increase** the capacitance of a parallel plate capacitor by:



Q: What is the **capacitance** between these two conducting structures?

A: The potential difference between them is V_0 . The **total charge** on one conducting structure is simply the sum of the charges on each plate:

